## **CLAIMS**

We claim:

1. A method of forming a heat spreader ball grid array package, comprising the steps:

providing a semiconductor chip affixed to a ball grid substrate; encasing the semiconductor chip over the ball grid substrate with a molding

compound;

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mounting a heat spreader over the ball grid substrate and spaced apart from the molding compound to form a gap; and

placing thermal grease into the gap at least between the heat spreader and the molding compound to form the heat spreader ball grid array package.

- 2. The method of claim 1, wherein the semiconductor chip is a silicon semiconductor chip, a germanium semiconductor chip or a silicon germanium semiconductor chip...
- 3. The method of claim 1, wherein the molding compound is comprised of epoxy resin and a curing agent; and the heat spreader is comprised of copper, aluminum, chromium plated on copper, chromium plated on aluminum, nickel plated on copper or nickel plated on aluminum.
- 4. The method of claim 1, wherein the molding compound is comprised of epoxy resin; and the heat spreader is comprised of copper.

- 5. The method of claim 1, wherein the thermal grease is comprised of silicon rubber containing heat-conducting particles.
- 6. The method of claim 1, wherein the heat-conducting particles comprises zinc oxide, aluminum oxide, aluminum nitride, boron nitride or ceramic fillers.
- 7. The method of claim 1, wherein the thermal grease is comprised of epoxy resin, curing agent, a catalyst, a coupling agent, a filler, a flame retardant, a mold-release agent, a coloring agent and a stress-relief agent.
- 8. The method of claim 1, wherein the molding compound has a coefficient of thermal expansion of from about 5 to 15; and the heat spreader has a coefficient of thermal expansion of from about 10 to 25.
- 9. The method of claim 1, wherein the molding compound has a coefficient of thermal expansion of about 7.0; and the heat spreader has a coefficient of thermal expansion of about 17.0.
- 10. The method of claim 1, including forming a pillar onto the ball grid substrate outboard of the semiconductor chip and the molding compound; wherein the heat spreader is mounted to the pillar.

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- 11. The method of claim 1, including forming a pillar onto the ball grid substrate outboard of the semiconductor chip and the molding compound; the pillar including a stiffener portion; wherein the heat spreader is mounted to the pillar.
- 12. The method of claim 1, including forming a pillar onto the ball grid substrate outboard of the semiconductor chip and the molding compound; the pillar including a copper stiffener portion; wherein the heat spreader is mounted to the pillar.
- 13. A method of forming a heat spreader ball grid array package, comprising the steps:

providing a semiconductor chip affixed to a ball grid substrate;

encasing the semiconductor chip over the ball grid substrate with a molding compound;

placing thermal grease over the semiconductor chip;

mounting a heat spreader over the ball grid substrate and thermal grease to form the heat spreader ball grid array package; and

mounting the heat spreader to a PCB substrate or stiffener using adhesive.

14. The method of claim 13, wherein the semiconductor chip is a silicon semiconductor chip, a germanium semiconductor chip or a silicon germanium semiconductor chip..

- 15. The method of claim 13, wherein the molding compound is comprised of epoxy resin and a curing agent; and the heat spreader is comprised of copper, aluminum, chromium plated on copper, chromium plated on aluminum, nickel plated on copper or nickel plated on aluminum.
- 16. The method of claim 13, wherein the molding compound is comprised of epoxy resin; and the heat spreader is comprised of copper.
- 17. The method of claim 13, wherein the thermal grease is comprised of silicon rubber containing heat-conducting particles.
- 18. The method of claim 13, wherein the heat-conducting particles comprises zinc oxide, aluminum oxide, aluminum nitride, boron nitride or ceramic fillers.
- 19. The method of claim 13, wherein the thermal grease is comprised of epoxy resin, curing agent, a catalyst, a coupling agent, a filler, a flame retardant, a mold-release agent, a coloring agent and a stress-relief agent.
- 20. The method of claim 13, wherein the molding compound has a coefficient of thermal expansion of from about 5 to 15; and the heat spreader has a coefficient of thermal expansion of from about 10 to 25.

- 21. The method of claim 13, wherein the molding compound has a coefficient of thermal expansion of about 7.0; and the heat spreader has a coefficient of thermal expansion of about 17.0.
- 22. The method of claim 13, including forming a pillar onto the ball grid substrate outboard of the semiconductor chip and the molding compound; wherein the heat spreader is mounted to the pillar.
- 23. The method of claim 13, including forming a pillar onto the ball grid substrate outboard of the semiconductor chip and the molding compound; the pillar including a stiffener portion; wherein the heat spreader is mounted to the pillar.
- 24. The method of claim 13, including forming a pillar onto the ball grid substrate outboard of the semiconductor chip and the molding compound; the pillar including a copper stiffener portion; wherein the heat spreader is mounted to the pillar.
- 25. A heat spreader ball grid array package, comprising:
  - a ball grid substrate;
  - a semiconductor chip affixed to the ball grid substrate;
- a molding compound encasing the semiconductor chip over the ball grid substrate;
  - a heat spreader mounted over the ball grid substrate and spaced apart from the molding compound to form a gap; and

thermal grease within the gap at least between the heat spreader and the molding compound.

- 26. The structure of claim 25, wherein the semiconductor chip is a silicon semiconductor chip, a germanium semiconductor chip or a silicon germanium semiconductor chip.
- 27. The structure of claim 25, wherein the molding compound is comprised of epoxy resin and a curing agent; and the heat spreader is comprised of copper, aluminum, chromium plated on copper, chromium plated on aluminum, nickel plated on copper or nickel plated on aluminum.
- 28. The structure of claim 25, wherein the molding compound is comprised of epoxy resin; and the heat spreader is comprised of copper.
- 29. The structure of claim 25, wherein the thermal grease is comprised of silicon rubber containing heat-conducting particles such as zinc oxide, aluminum oxide, aluminum nitride, boron nitride or ceramic fillers or other materials which have the properties of heat conduction.
- 30. The structure of claim 25, wherein the thermal grease is comprised of epoxy resin, curing agent, a catalyst, a coupling agent, a filler, a flame retardant, a mold-release agent, a coloring agent and a stress-relief agent.

- 31. The structure of claim 25, wherein the thermal grease is comprised of epoxy resin, curing agent, a catalyst and a coupling agent.
- 32. The structure of claim 25, wherein the molding compound has a coefficient of thermal expansion of from about 5 to 15; and the heat spreader has a coefficient of thermal expansion of from about 10 to 25.
- 33. The structure of claim 25, wherein the molding compound has a coefficient of thermal expansion of about 7.0; and the heat spreader has a coefficient of thermal expansion of about 17.0.
- 34. The structure of claim 25, wherein the semiconductor chip is a silicon semiconductor chip and has a coefficient of thermal expansion of from about 2.5 to 3.5.
- 35. The structure of claim 25, wherein the heat spreader has a shape of an inverted square pie tin having an elongated surrounding lip.
- 36. The structure of claim 25, wherein the heat spreader has a shape of an inverted square pie tin having elongated surrounding lip; the heat spreader being mounted onto the ball grid substrate at the elongated surrounding lip using epoxy adhesive.

- 37. The structure of claim 25, wherein the heat spreader has a shape of an inverted square pie tin having an elongated surrounding lip; and wherein the thermal grease nearly fills the gap.
- 38. The structure of claim 25, further including a pillar formed onto the ball grid substrate outboard of the semiconductor chip and the molding compound; wherein the heat spreader is mounted to the pillar.
- 39. The structure of claim 25, further including a pillar formed onto the ball grid substrate outboard of the semiconductor chip and the molding compound; the pillar including a stiffener portion; wherein the heat spreader is mounted to the pillar.
- 40. The structure of claim 25, further including a pillar formed onto the ball grid substrate outboard of the semiconductor chip and the molding compound; the pillar including a copper stiffener portion; wherein the heat spreader is mounted to the pillar.
- 41. A heat spreader ball grid array package, comprising:
  - a ball grid substrate;

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- a semiconductor chip affixed to the ball grid substrate;
- a molding compound encasing the semiconductor chip over the ball grid substrate;

thermal grease over the molding compound;

- a heat spreader mounted over the ball grid substrate, the molding compound and the thermal grease; and
  - a PCB substrate or a stiffener mounted to the heat spreader.
- 42. The structure of claim 41, wherein the semiconductor chip is a silicon semiconductor chip, a germanium semiconductor chip or a silicon germanium semiconductor chip.
- 43. The structure of claim 41, wherein the molding compound is comprised of epoxy resin and a curing agent; and the heat spreader is comprised of copper, aluminum, chromium plated on copper, chromium plated on aluminum, nickel plated on copper or nickel plated on aluminum.
- 44. The structure of claim 41, wherein the molding compound is comprised of epoxy resin; and the heat spreader is comprised of copper.
- 45. The structure of claim 41, wherein the thermal grease is comprised of silicon rubber containing heat-conducting particles such as zinc oxide, aluminum oxide, aluminum nitride, boron nitride or ceramic fillers or other materials which have the properties of heat conduction.
- 46. The structure of claim 41, wherein the thermal grease is comprised of epoxy resin, curing agent, a catalyst, a coupling agent, a filler, a flame retardant, a mold-release agent, a coloring agent and a stress-relief agent.

- 47. The structure of claim 41, wherein the thermal grease is comprised of epoxy resin, curing agent, a catalyst and a coupling agent.
- 48. The structure of claim 41, wherein the molding compound has a coefficient of thermal expansion of from about 5 to 15; and the heat spreader has a coefficient of thermal expansion of from about 10 to 25.
- 49. The structure of claim 41, wherein the molding compound has a coefficient of thermal expansion of about 7.0; and the heat spreader has a coefficient of thermal expansion of about 17.0.
- 50. The structure of claim 41, wherein the semiconductor chip is a silicon semiconductor chip and has a coefficient of thermal expansion of from about 2.5 to 3.5.
- 51. The structure of claim 41, wherein the heat spreader has a shape of an inverted square pie tin having an elongated surrounding lip.
- 52. The structure of claim 41, wherein the heat spreader has a shape of an inverted square pie tin having elongated surrounding lip; the heat spreader being mounted onto the ball grid substrate at the elongated surrounding lip using epoxy adhesive.

53. The structure of claim 41, wherein the heat spreader has a shape of an inverted square pie tin having an elongated surrounding lip; and wherein the thermal grease nearly fills the distance between the molding compound and the heat spreader.

54. The structure of claim 41, further including a pillar formed onto the ball grid substrate outboard of the semiconductor chip and the molding compound; wherein the heat spreader is mounted to the pillar.

55. The structure of claim 41, further including a pillar formed onto the ball grid substrate outboard of the semiconductor chip and the molding compound; the pillar including a stiffener portion; wherein the heat spreader is mounted to the pillar.

56. The structure of claim 41, further including a pillar formed onto the ball grid substrate outboard of the semiconductor chip and the molding compound; the pillar including a copper stiffener portion; wherein the heat spreader is mounted to the pillar.